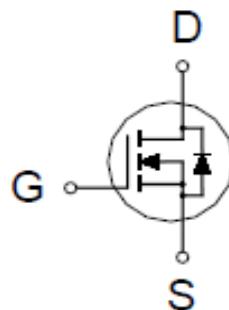
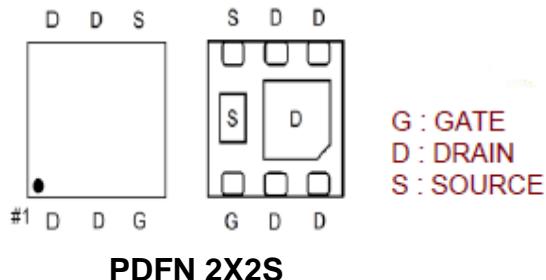


PB600BA

N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	12mΩ @ $V_{GS} = 10V$	9A



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ²	I_D	9	A
		7.2	
Pulsed Drain Current ¹	I_{DM}	27	
Avalanche Current	I_{AS}	12.6	
Avalanche Energy	E_{AS}	7.9	mJ
Power Dissipation	P_D	1.7	W
		1.1	
Operating Junction & Storage Temperature Range	T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$R_{\theta JA}$		71.7	°C / W

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Coppe.

PB600BA N-Channel Enhancement Mode MOSFET

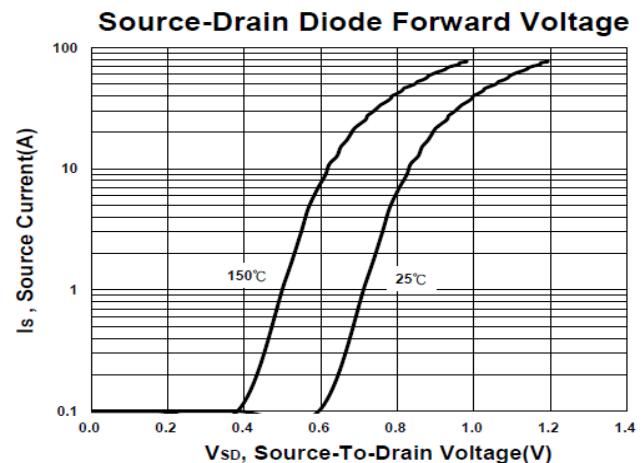
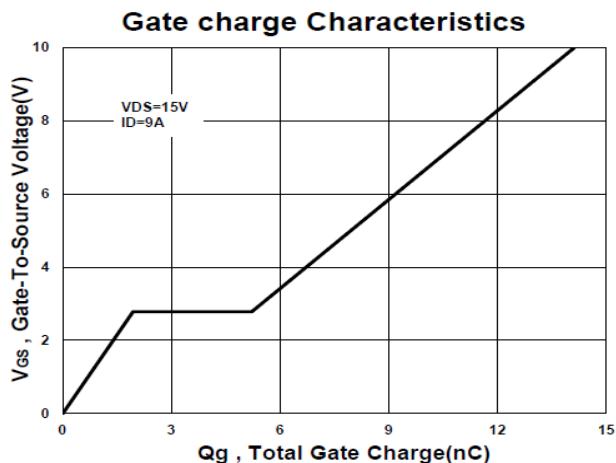
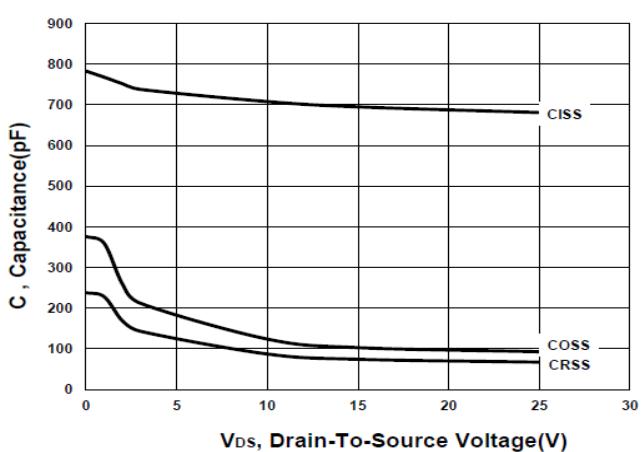
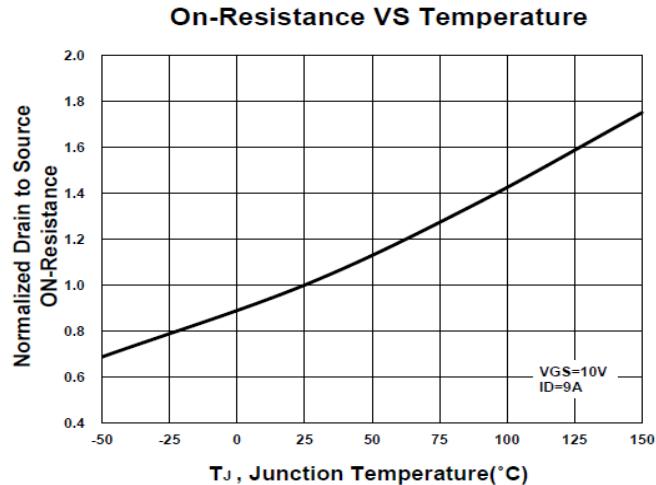
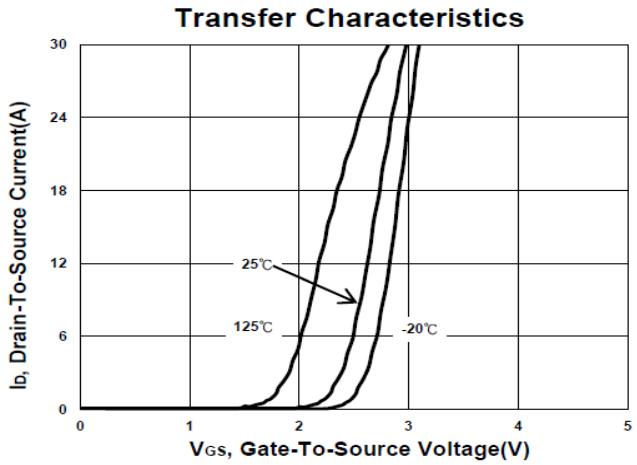
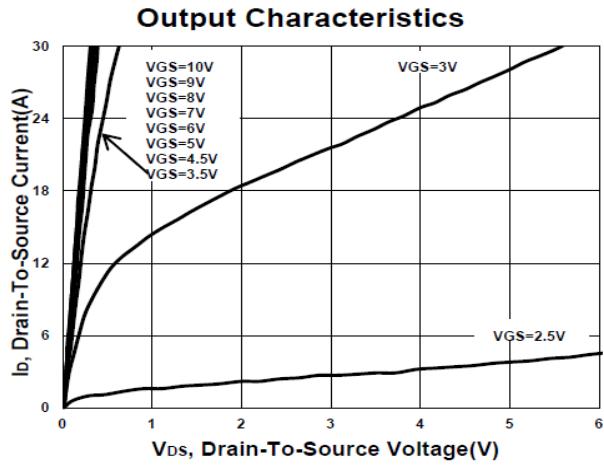
ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	30			V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1.3	1.7	2.5	
Gate-Body Leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 24\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
		$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 55^\circ\text{C}$			10	
Drain-Source On-State Resistance ¹	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}} = 4.5\text{V}, I_D = 9\text{A}$		11	17.5	$\text{m}\Omega$
		$V_{\text{GS}} = 10\text{V}, I_D = 9\text{A}$		9	12	
Forward Transconductance ¹	g_{fs}	$V_{\text{DS}} = 10\text{V}, I_D = 9\text{A}$	45			S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 15\text{V}, f = 1\text{MHz}$		706		pF
Output Capacitance	C_{oss}			103		
Reverse Transfer Capacitance	C_{rss}			74		
Gate Resistance	R_g	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 0\text{V}, f = 1\text{MHz}$		3.1		Ω
Total Gate Charge ²	$Q_{\text{g}}(V_{\text{GS}}=10\text{V})$	$V_{\text{DS}} = 15\text{V}, I_D = 9\text{A}$		15		nC
	$Q_{\text{g}}(V_{\text{GS}}=4.5\text{V})$			8		
Gate-Source Charge ²	Q_{gs}			2.6		
Gate-Drain Charge ²	Q_{gd}			3.6		
Turn-On Delay Time ²	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 15\text{V}$ $I_D \geq 9\text{A}, V_{\text{GEN}} = 10\text{V}, R_G = 6\Omega$		13		nS
Rise Time ²	t_r			37		
Turn-Off Delay Time ²	$t_{\text{d}(\text{off})}$			48		
Fall Time ²	t_f			25		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ\text{C}$)						
Continuous Current	I_S				1.5	A
Forward Voltage ¹	V_{SD}	$I_F = 9\text{A}, V_{\text{GS}} = 0\text{V}$			1.1	V
Reverse Recovery Time	t_{rr}	$I_F = 9\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		11		nS
Reverse Recovery Charge	Q_{rr}			3		nC

¹Pulse test : Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.

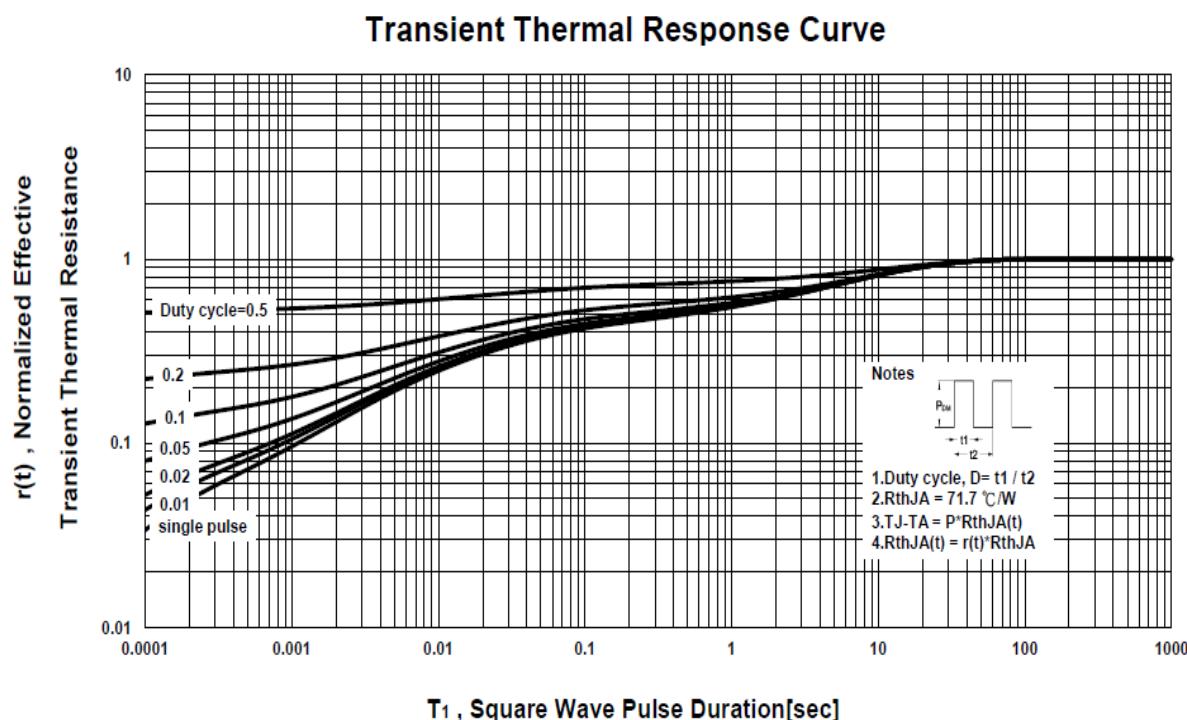
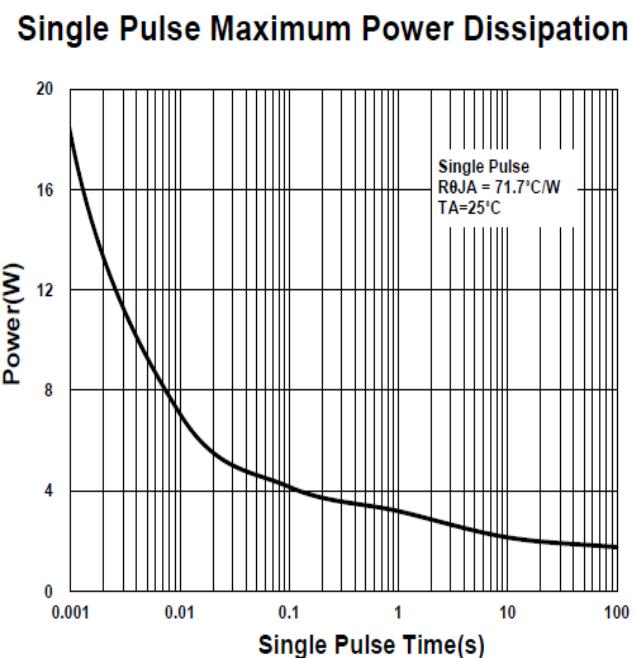
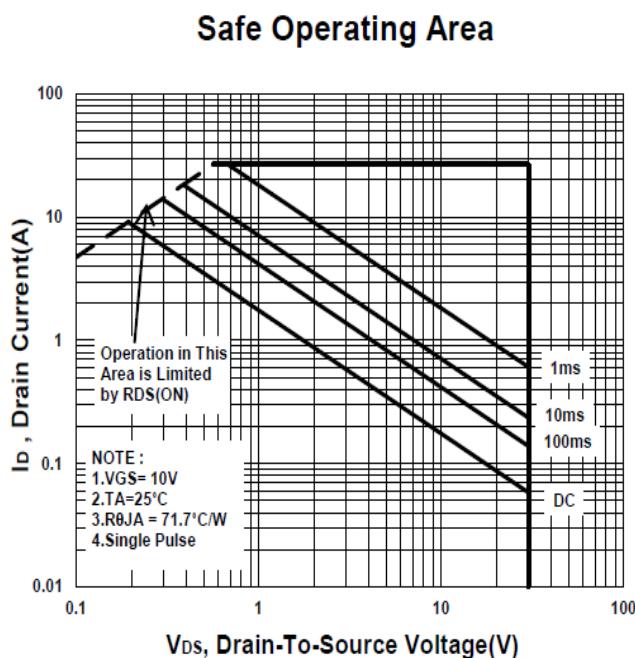
²Independent of operating temperature.

PB600BA N-Channel Enhancement Mode MOSFET



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Package Dimension

PDFN 2x2S MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	1.9		2.1	H	0.8		1.1
B	1.9		2.1	I	0		0.05
C	0.55	0.65	0.75	J		0.203	
D	0.85		1.1	K	0.7		0.8
E	0.174	0.25	0.326	L	0.2		0.4
F	0.25		0.35	M	0.46		0.85
G		0.2					

